

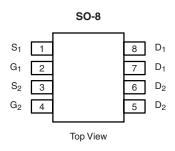
Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 30	0.080 at V _{GS} = - 10 V	- 3.9		
	0.135 at V _{GS} = - 4.5 V	- 3.0		

FEATURES

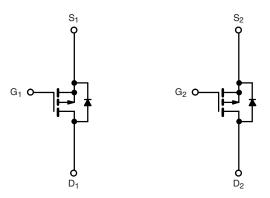
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4947ADY-T1-E3 (Lead (Pb)-free)

Si4947ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 30		٧	
Gate-Source Voltage		V _{GS}	± 20			
Continuous Drain Current /T 150 °C\2	T _A = 25 °C	- I _D	- 3.9	- 3.0		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 3.1	- 2.4		
Pulsed Drain Current		I _{DM}	- 20		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.7	- 1.0	l	
Marian ma Damer Dissipations	T _A = 25 °C	- P _D	2.0	1.2	· W	
Maximum Power Dissipation ^a	T _A = 70 °C		1.3	0.76		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 10 s	- R _{thJA}	54	62.5		
Maximum Junction-to-Ambient ^a	Steady State		87	105	°C/W	
Maximum Junction-to-Foot	Steady State	R _{thJF}	34	45		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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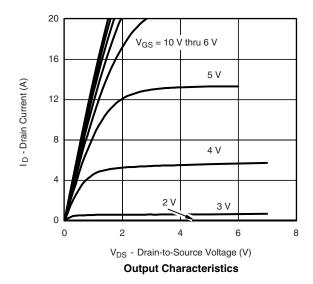
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 1.0			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zava Cata Valtaga Dvain Current	1	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μА	
Zero Gate Voltage Drain Current	IDSS	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 70 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 15			Α	
D : 0	D	V _{GS} = - 10 V, I _D = - 3.9 A		0.062	0.080	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -3.0 \text{ A}$		0.105	0.135		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 2.5 A		5.0		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.7 A, V _{GS} = 0 V		- 0.82	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			5.8	8		
Gate-Source Charge	Q _{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -3.9 \text{ A}$		2		nC	
Gate-Drain Charge	Q _{gd}			1.9			
Turn-On Delay Time	t _{d(on)}			8	15		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		9	18		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω		21	40	ns	
Fall Time	t _f			10	20		
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = -1.7 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		27	40		

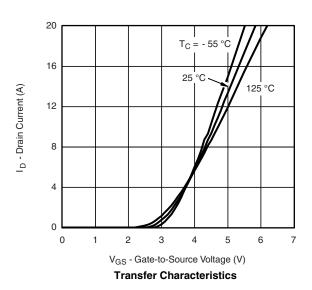
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

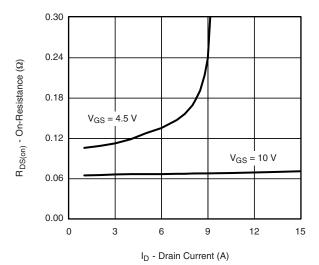
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



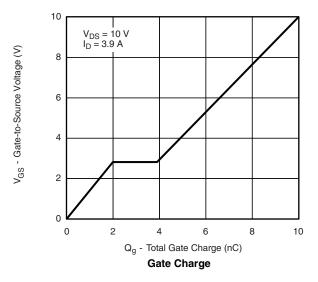


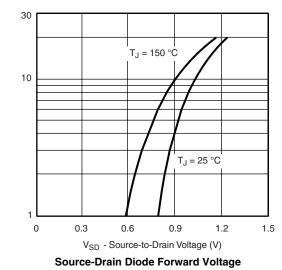


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On-Resistance vs. Drain Current

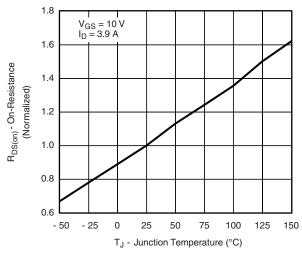




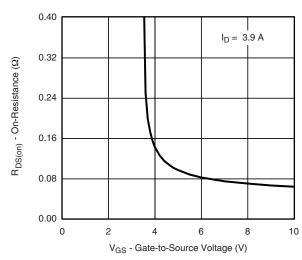
1000 800 C_{iss} 600 400 200 C_{rss} 0 6 12 18 24 30

V_{DS} - Drain-to-Source Voltage (V)





On-Resistance vs. Junction Temperature



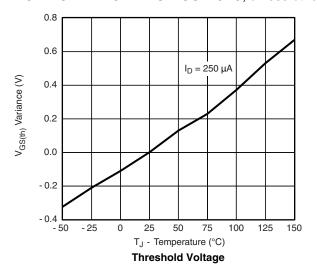
On-Resistance vs. Gate-to-Source Voltage

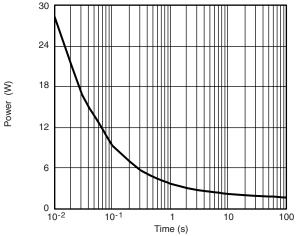
Is - Source Current (A)

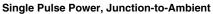
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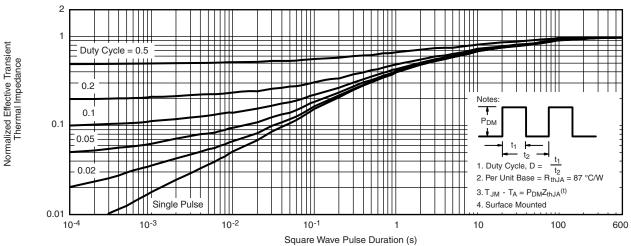
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

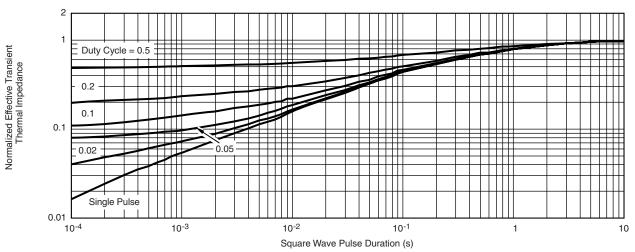








Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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